

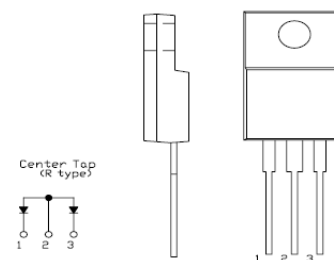
MBRF30100CTR SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

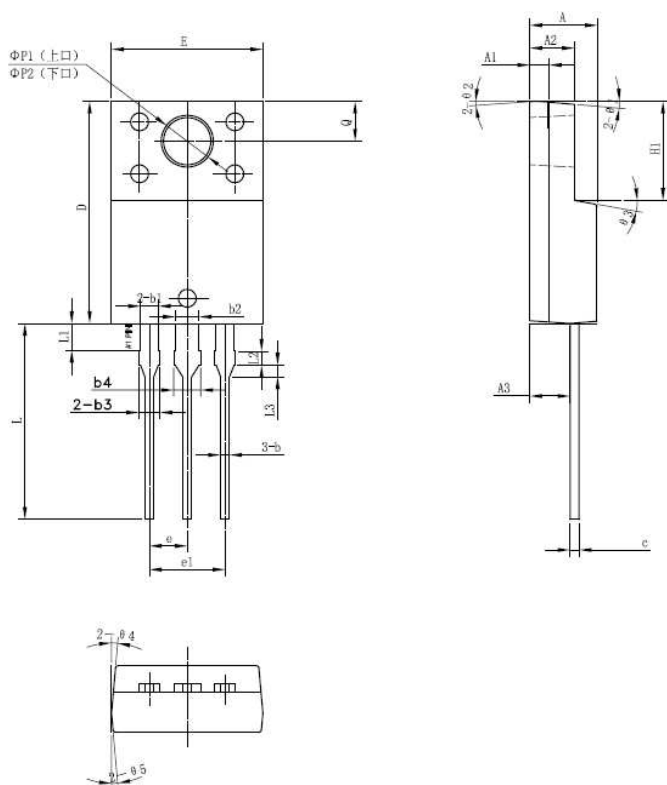
Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



OUTLINE DRAWING

Mechanical Dimensions: In mm



SYMBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

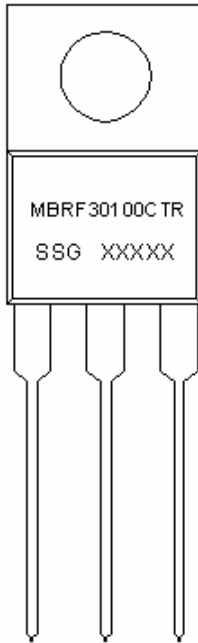
ITO-220AB(HD)



Technical Data
Data Sheet N0853, Rev. A

Green Products

Marking Diagram:



Where XXXXX is YYWWL

- MBR = Device Type
- F = Package type
- 30 = Forward Current (30A)
- 100 = Reverse Voltage (100V)
- CTR = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRF30100CTR	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 133^\circ\text{C}$, rectangular wave form	30	A
Peak Repetitive Forward Current(per leg)	I_{FRM}	Rated V_R square wave, 20KHz $T_C = 133^\circ\text{C}$	20	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	Surge applied at rated load conditions halfwave, single phase,60Hz	200	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V _{F1}	@ 15 A, Pulse, T _J = 25 °C	0.85	V
	V _{F2}	@ 15 A, Pulse, T _J = 125 °C	0.70	V
Reverse Current (per leg) *	I _{R1}	@V _R = rated V _R T _J = 25 °C	1.00	mA
	I _{R2}	@V _R = rated V _R T _J = 125 °C	6.0	mA
Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	400	pF
Series Inductance(per leg)	L _S	Measured lead to lead 5 mm from package body	8.0	nH
Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	2.0	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θJA}	DC operation	50	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased	0.50	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

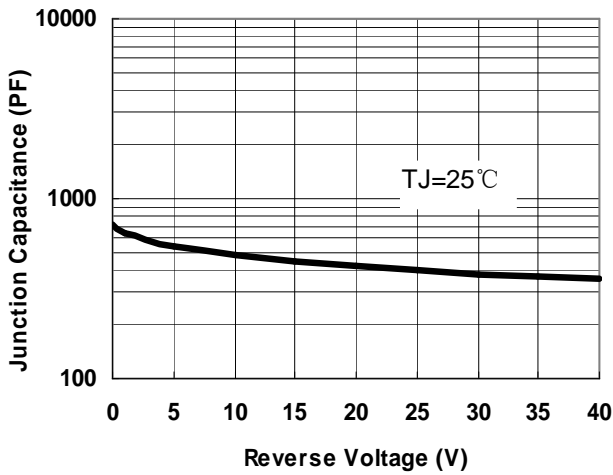


Fig.1-Typical Junction Capacitance

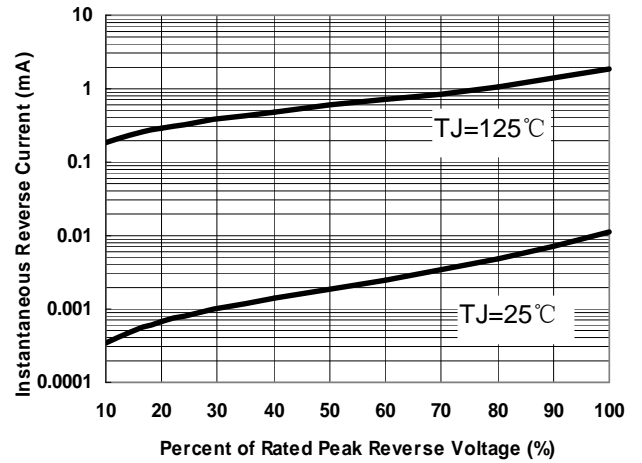


Fig.2-Typical Reverse Characteristics

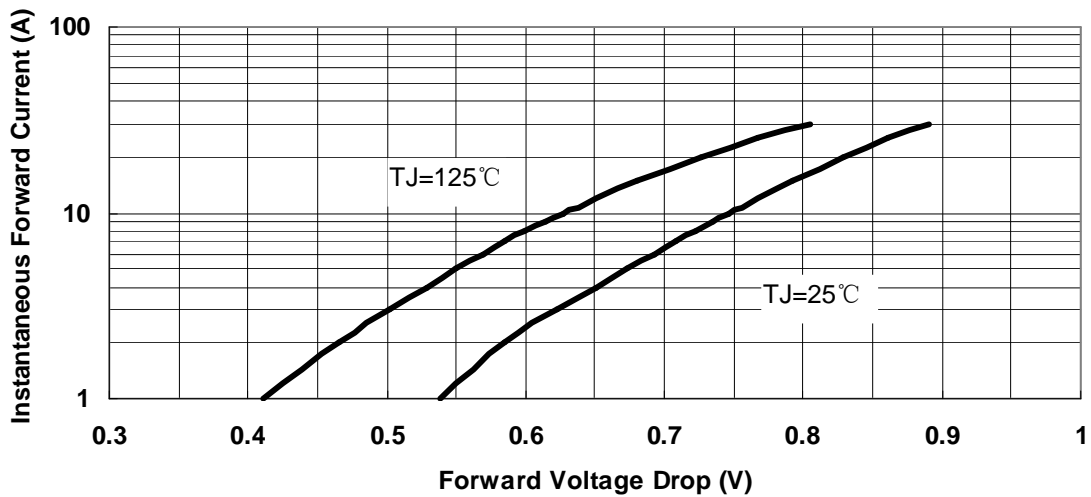


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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